Supporting Information

Modification in Structure, Phase Transition and Magnetic Property of Metallic Gallium Driven by Atom-Molecule Interactions

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A list of the contents for all the supporting information

Figure 1 Photographs of (a) Ga−0, (b) Ga−1a, (c) Ga−1b, (d) Ga−1c and (e) Ga−1d.

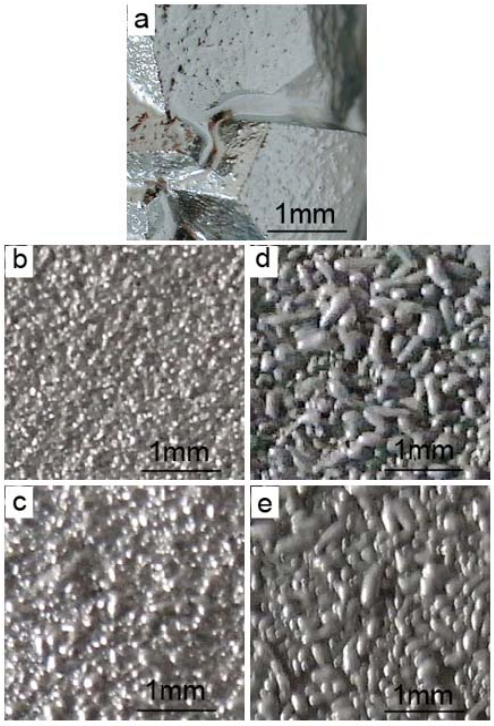

Figure 2 TG (A) and DTG (B) profiles of (a) *β*-CD and (b) Ga−3a.

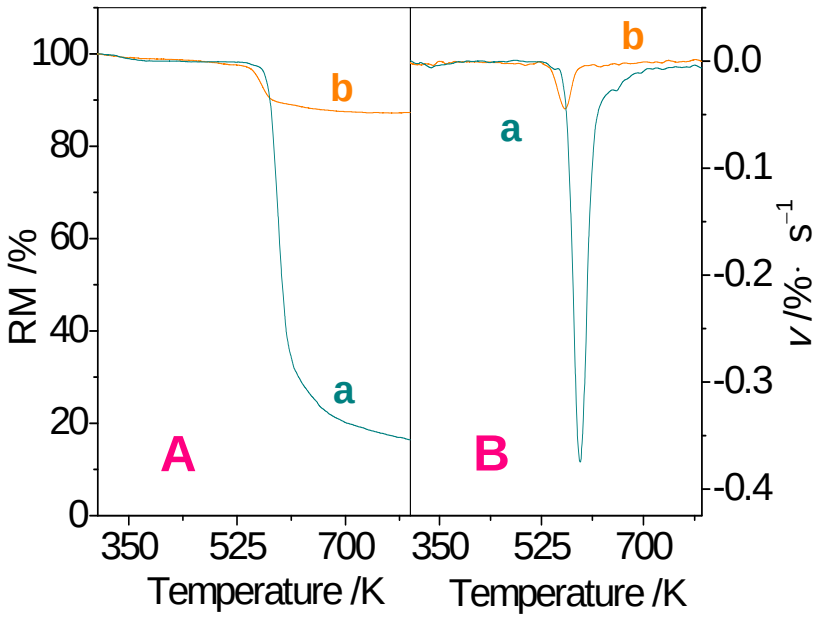

Figure 3 Raman spectra of the residual products (a) *β*-CD and (b) Ga−3f after sintering at 773.2 K for 0.5 h in nitrogen.

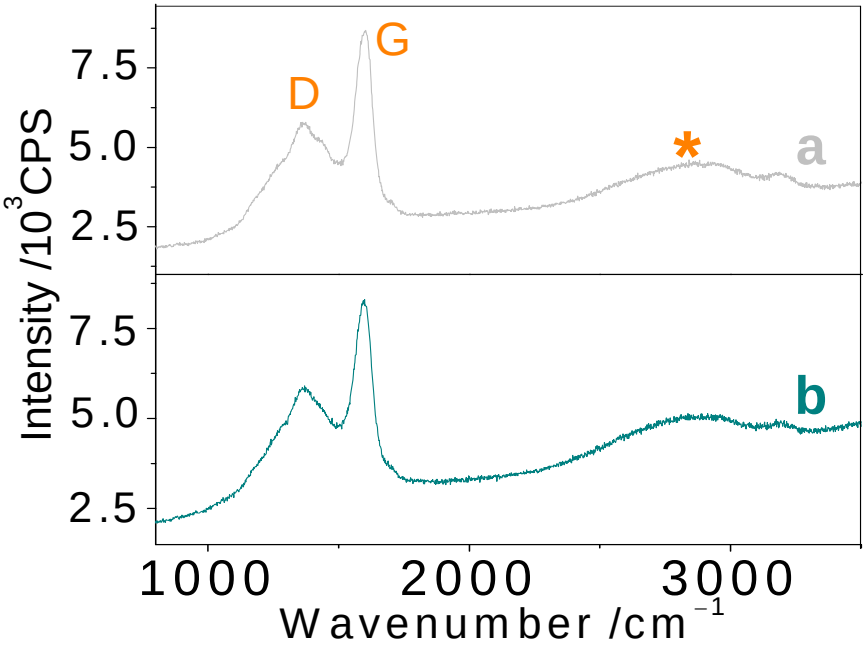

Figure 4 XRD patterns of the residual products (a) *β*-CD and (b) Ga−3f after sintering at 773.2 K for 0.5 h in nitrogen.

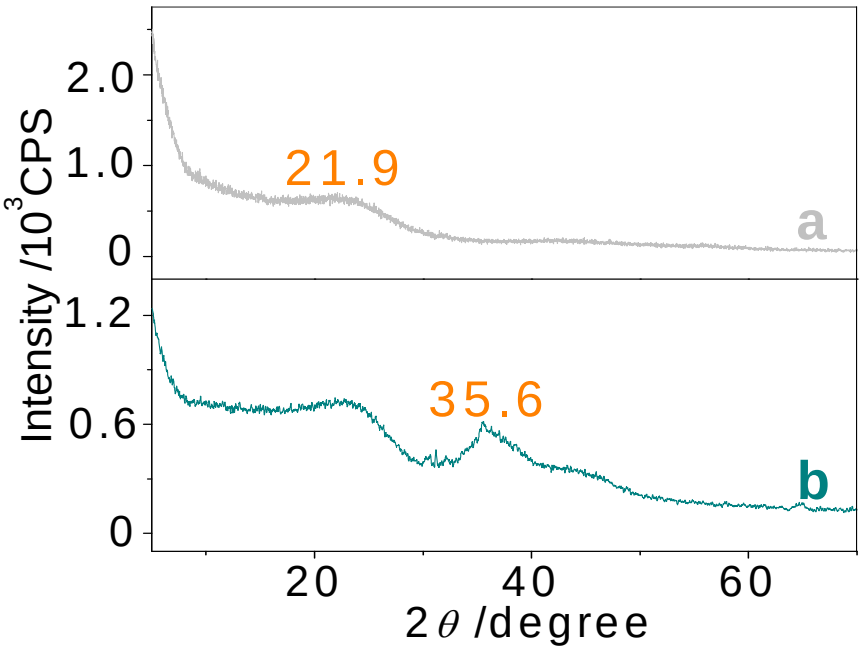

Table 1 Binding energies (eV) of some core levels in Ga–3f.

Sample	Binding energy (eV)				
	Ga 3d	Ga $2p_{3/2}$	Ga $2p_{1/2}$	C 1s	O 1s
Ga–3f	21.4	1119.2	1146.0	284.8	533.2

Figure 5 Continuous DSC heating and cooling curves of Ga–3e in the second cycle.